

<<纳米晶体管>>

图书基本信息

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## <<纳米晶体管>>

### 内容概要

近几十年来，晶体管的尺度发展一直是推动电子学的动力，各种分子尺度的器件已经出现，甚至有取代硅晶体管的趋势。

本书详细介绍了纳米晶体管的理论、建模与仿真，内容包括弹道纳米晶体管的弹道传输和量子效应，MOSFET的散射理论等。

为了详细说明纳米晶体管，本书还提供了已被详尽数值仿真所证实的物理图片及半解析模型。

本书可供从事纳米电子器件领域的电子工程师、物理学者和化学家参考。

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